What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	eZ8
Core Size	8-Bit
Speed	20MHz
Connectivity	IrDA, UART/USART
Peripherals	Brown-out Detect/Reset, LED, LVD, POR, PWM, WDT
Number of I/O	17
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	128 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 3.6V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	20-SOIC (0.295", 7.50mm Width)
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/zilog/z8f041ash020eg

Warning: DO NOT USE THIS PRODUCT IN LIFE SUPPORT SYSTEMS.

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As used herein

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

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Rate Generator to function as an additional counter if the UART functionality is not employed.

UART Baud Rate Generator

The UART Baud Rate Generator creates a lower frequency baud rate clock for data transmission. The input to the Baud Rate Generator is the system clock. The UART Baud Rate High and Low Byte registers combine to create a 16-bit baud rate divisor value (BRG[15:0]) that sets the data transmission rate (baud rate) of the UART. The UART data rate is calculated using the following equation:

$$\text{UART Data Rate (bits/s)} = \frac{\text{System Clock Frequency (Hz)}}{16 \times \text{UART Baud Rate Divisor Value}}$$

When the UART is disabled, the Baud Rate Generator functions as a basic 16-bit timer with an interrupt upon time-out. Observe the following steps to configure the Baud Rate Generator as a timer with an interrupt upon time-out:

1. Disable the UART by clearing the REN and TEN bits in the UART Control 0 Register to 0.
2. Load the acceptable 16-bit count value into the UART Baud Rate High and Low Byte registers.
3. Enable the Baud Rate Generator timer function and associated interrupt by setting the ***BRGCTL*** bit in the UART Control 1 Register to 1.

When configured as a general purpose timer, the interrupt interval is calculated using the following equation:

$$\text{Interrupt Interval}(s) = \text{System Clock Period (s)} \times BRG[15:0]$$

UART Control Register Definitions

The UART Control registers support the UART and the associated Infrared Encoder/Decoders. For more information about infrared operation, see the Infrared Encoder/Decoder chapter on page 120.

UART Control 0 and Control 1 Registers

The UART Control 0 (UxCTL0) and Control 1 (UxCTL1) registers, shown in Tables 63 and 64, configure the properties of the UART’s transmit and receive operations. The UART Control registers must not be written while the UART is enabled.

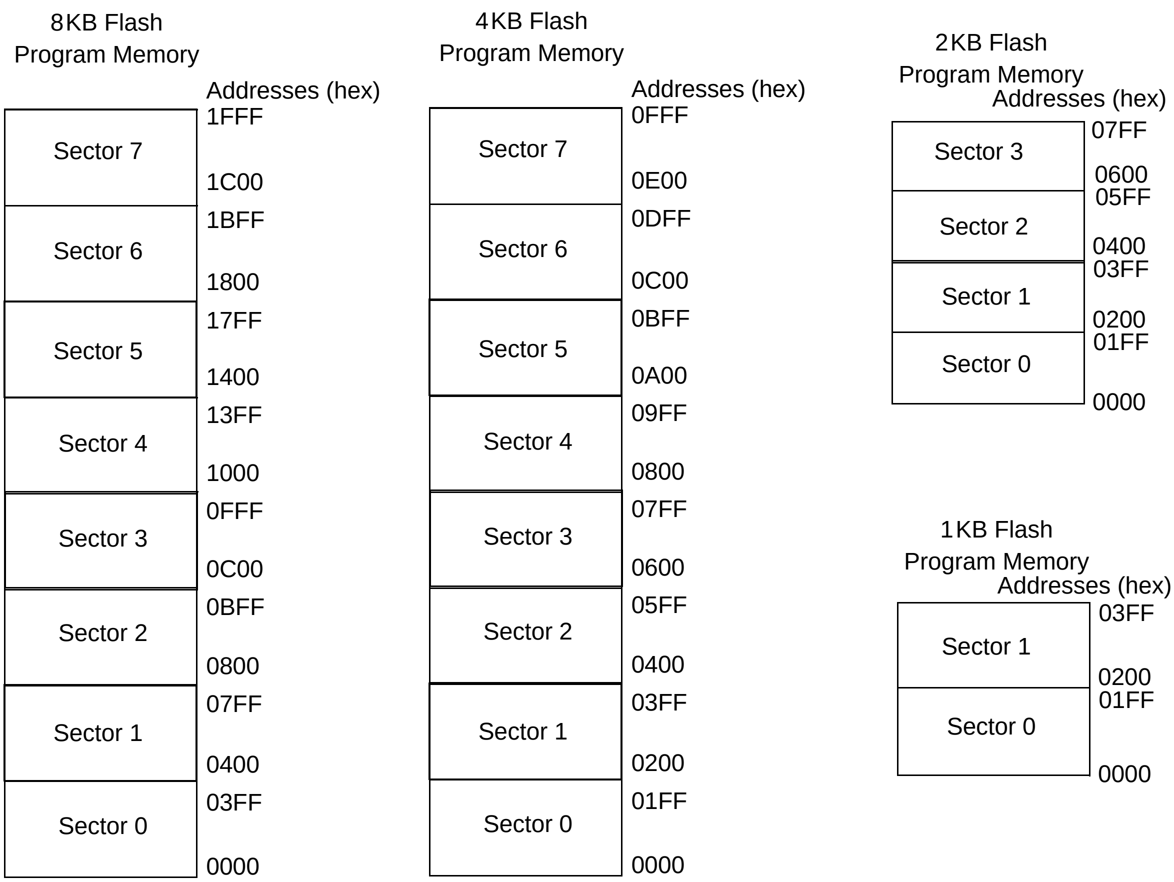

Figure 21. Flash Memory Arrangement

Flash Information Area

The Flash information area is separate from Program Memory and is mapped to the address range FE00H to FFFFH. This area is readable but cannot be erased or overwritten. Factory trim values for the analog peripherals are stored here. Factory calibration data for the ADC is also stored here.

Operation

The Flash Controller programs and erases Flash memory. The Flash Controller provides the proper Flash controls and timing for Byte Programming, Page Erase and Mass Erase of Flash memory.

The Flash Controller contains several protection mechanisms to prevent accidental programming or erasure. These mechanism operate on the page, sector and full-memory levels.

Flash Controller Behavior in DEBUG Mode

The following changes in behavior of the Flash Controller occur when the Flash Controller is accessed using the On-Chip Debugger:

- The Flash Write Protect option bit is ignored.
- The Flash Sector Protect Register is ignored for programming and erase operations.
- Programming operations are not limited to the page selected in the Page Select Register.
- Bits in the Flash Sector Protect Register can be written to one or zero.
- The second write of the Page Select Register to unlock the Flash Controller is not necessary.
- The Page Select Register can be written when the Flash Controller is unlocked.
- The Mass Erase command is enabled through the Flash Control Register.

! **Caution:** For security reasons, the Flash controller allows only a single page to be opened for write/erase. When writing multiple Flash pages, the flash controller must go through the unlock sequence again to select another page.

Flash Control Register Definitions

This section defines the features of the following Flash Control registers.

Flash Control Register: see page 153

Flash Status Register: see page 155

Flash Page Select Register: see page 156

Flash Sector Protect Register: see page 157

Flash Frequency High and Low Byte Registers: see page 157

Flash Control Register

The Flash Controller must be unlocked using the Flash Control (FCTL) Register before programming or erasing the Flash memory. Writing the sequence 73H 8CH, sequentially, to the Flash Control Register unlocks the Flash Controller. When the Flash Controller is unlocked, the Flash memory can be enabled for Mass Erase or Page Erase by writing the appropriate enable command to the FCTL. Page Erase applies only to the active page selected in Flash Page Select Register. Mass Erase is enabled only through the On-Chip

Table 97. ADC Calibration Data Location (Continued)

Info Page Address	Memory Address	Compensation Usage	ADC Mode	Reference Type
12	FE12	Positive Gain High Byte	Differential Unbuffered	Internal 2.0 V
13	FE13	Positive Gain Low Byte	Differential Unbuffered	Internal 2.0 V
30	FE30	Negative Gain High Byte	Differential Unbuffered	Internal 2.0 V
31	FE31	Negative Gain Low Byte	Differential Unbuffered	Internal 2.0 V
72	FE72	Offset	Differential Unbuffered	Internal 1.0 V
14	FE14	Positive Gain High Byte	Differential Unbuffered	Internal 1.0 V
15	FE15	Positive Gain Low Byte	Differential Unbuffered	Internal 1.0 V
32	FE32	Negative Gain High Byte	Differential Unbuffered	Internal 1.0 V
33	FE33	Negative Gain Low Byte	Differential Unbuffered	Internal 1.0 V
75	FE75	Offset	Differential Unbuffered	External 2.0 V
16	FE16	Positive Gain High Byte	Differential Unbuffered	External 2.0 V
17	FE17	Positive Gain Low Byte	Differential Unbuffered	External 2.0 V
34	FE34	Negative Gain High Byte	Differential Unbuffered	External 2.0 V
35	FE35	Negative Gain Low Byte	Differential Unbuffered	External 2.0 V
78	FE78	Offset	Differential 1x Buffered	Internal 2.0 V
18	FE18	Positive Gain High Byte	Differential 1x Buffered	Internal 2.0 V
19	FE19	Positive Gain Low Byte	Differential 1x Buffered	Internal 2.0 V
36	FE36	Negative Gain High Byte	Differential 1x Buffered	Internal 2.0 V
37	FE37	Negative Gain Low Byte	Differential 1x Buffered	Internal 2.0 V
7B	FE7B	Offset	Differential 1x Buffered	External 2.0 V
1A	FE1A	Positive Gain High Byte	Differential 1x Buffered	External 2.0 V
1B	FE1B	Positive Gain Low Byte	Differential 1x Buffered	External 2.0 V
38	FE38	Negative Gain High Byte	Differential 1x Buffered	External 2.0 V
39	FE39	Negative Gain Low Byte	Differential 1x Buffered	External 2.0 V

Byte Write

To write a byte to the NVDS array, the user code must first push the address, then the data byte onto the stack. The user code issues a CALL instruction to the address of the byte-write routine (0x10B3). At the return from the sub-routine, the write status byte resides in working register R0. The bit fields of this status byte are defined in Table 106. The contents of the status byte are undefined for write operations to illegal addresses. Also, user code must pop the address and data bytes off the stack.

The write routine uses 13 bytes of stack space in addition to the two bytes of address and data pushed by the user. Sufficient memory must be available for this stack usage.

Because of the Flash memory architecture, NVDS writes exhibit a nonuniform execution time. In general, a write takes 251 µs (assuming a 20 MHz system clock). Every 400 to 500 writes, however, a maintenance operation is necessary. In this rare occurrence, the write takes up to 61 ms to complete. Slower system clock speeds result in proportionally higher execution times.

NVDS byte writes to invalid addresses (those exceeding the NVDS array size) have no effect. Illegal write operations have a 2 µs execution time.

Table 106. Write Status Byte

Bit	**7**	**6**	**5**	**4**	**3**	**2**	**1**	**0**
Field	Reserved				RCPY	PF	AWE	DWE
Default Value	0	0	0	0	0	0	0	0

Bit	Description
[7:4]	**Reserved** These bits are reserved and must be programmed to 0000.
[3] RCPY	**Recopy Subroutine Executed** A recopy subroutine was executed. These operations take significantly longer than a normal write operation.
[2] PF	**Power Failure Indicator** A power failure or system reset occurred during the most recent attempted write to the NVDS array.
[1] AWE	**Address Write Error** An address byte failure occurred during the most recent attempted write to the NVDS array.
[0] DWE	**Data Write Error** A data byte failure occurred during the most recent attempted write to the NVDS array.